

Amendments to the Specification:

Please amend the specification as follows:

Please replace the second full paragraph on page 1, lines 7-15, with the following rewritten paragraph:

A semiconductor photo mask is used for exposing a circuit pattern on a wafer in a manufacturing process of a semiconductor device, a liquid crystal display device, etc. A semiconductor photo mask is a transparent ~~semiconductor~~ substrate on that a minute pattern film, which is an opaque film, is formed. When the pattern film is formed on the substrate, two types of defects may occur: a white defect or a ~~deficient~~ clear defect, at which a part of the pattern film is lost, and a black defect or ~~a surplus~~ an opaque defect, at which the substrate is unnecessarily covered with film.

Please replace the first full paragraph on page 2, lines 8-10, with the following rewritten paragraph:

On the other hand, black defects, namely unnecessary part of pattern film, is conventionally vaporized to correct a semiconductor photo mask by irradiating laser light on the part.

Please replace the paragraph bridging pages 9 and 10, starting on page 9, line 22 and ending on page 10, line 4, with the following rewritten paragraph:

~~AN~~ A sucking unit 9 is fixed on the X-Y stage 8 to adhere to and hold the substrate 16. The following description shows detailed structure of the sucking unit 9. As shown in Fig. 3, the sucking unit 9 includes an sucking mount 30 that has a square frame shape. A 3-mm thickness translucent cover 31 is embedded in the top of the frame of the sucking mount 30. Female screws 32 for fixing the sucking mount 30 on the X-Y stage 8 are embedded on the top of the sucking mount 30. An o-ring groove 33 is cut around the inside of the sucking mount 30 under the translucent cover 31. A rubbery o-ring 34 is

embedded in the o-ring groove 33 in order to keep the space between the sucking unit 9 and the substrate 16 airtight.

Please replace the third full paragraph on page 10, lines 20-23, with the following rewritten paragraph:

Turning again to Fig. 1, an image-processing unit 13, ~~which is drawn in dotted line in Fig. 1,~~ takes image of the substrate 16 on the handler 14 in order to confirm whether the substrate 16 is put on a stand of the handler 14 at a correct position.

Please replace the first full paragraph on page 13, lines 7-19, with the following rewritten paragraph:

When all of the white defects on the substrate 16 are corrected, the operator stops providing CVD gas and only provides purge gas. Next, the controller 15 directs the X-Y stage 8 to move a black defect on the substrate 16 just above the laser-irradiating hole 25 of the gas window 6. The operator observes the black defect on the substrate 16 by the laser irradiator/microscope optical unit 3 with her/his own eyes to make sure, and next, exactly tunes in size, angle and position of a slit for irradiating laser of the laser irradiator/microscope optical unit 3. Then, the laser source 1, which irradiates laser light for vaporizing film, irradiates two shots of laser light at the ~~white~~ black defect to vaporize unnecessary part of pattern film. These processes are repeated for all of the black defects on the substrate 16.

Please replace the second full paragraph on page 17, lines 11-20, with the following rewritten paragraph:

According to the pattern-correcting device mentioned above, the surface processed for correcting defects faces downward when the surface is held by the sucking unit 9 in order to correct white defects on a photo mask by laser CVD. Consequently, the pattern-correcting device can prevent from sticking

again particles caused by laser CVD on the substrate 16. The difference between the area on the substrate 16 irradiated by laser light and the area on the substrate 16 covered with film is smaller. The fluctuation of the ~~are~~ area covered with film is smaller. As a result, the pattern-correcting device can process photo mask with high accuracy.